

IN THE CLAIMS:

Please cancel Claims 5 to 7, 16 to 18 and 46 without prejudice or disclaimer of the subject matter presented therein and without conceding the correctness of their rejections. Please amend Claims 1, 8 to 12, 19 to 26, 34, 36 and 44 as shown below. The claims, as pending in the subject application, read as follows:

1. (Re-presented - Formerly Dependent Claim 6) A structure having pores comprising:

a substrate;

a plurality of electroconductive layers formed on a surface of the substrate;

a layer containing aluminum oxide covering the plurality of electroconductive layers and the surface of the substrate where no electroconductive layer is formed; and

a plurality of pores formed in the layer containing aluminum oxide;

wherein the plurality of pores are is disposed above the plurality of electroconductive layers and the surface of the substrate where no electroconductive layer is formed, with a part of the layer containing aluminum oxide provided under the plurality of pores; and

wherein the layer containing aluminum oxide provided between the bottom of the pores disposed above the electroconductive layer and the electroconductive layer comprises a material forming the electroconductive layer; and

wherein a material different from aluminum oxide is filled in at least one pore disposed above the electroconductive layer.

2. (Original) A structure having pores according to claim 1, wherein the electroconductive layer comprises at least one element selected from the group consisting of Ti, Zr, Hf, Nb, Ta, Mo, and W.

3. (Original) A structure having pores according to either one of claims 1 and 2, wherein the substrate comprises an insulating material.

4. (Original) A structure having pores according to either one of claims 1 and 2, wherein the substrate comprises an electroconductive substrate and a film composed of an insulating material provided on a surface of the electroconductive substrate.

5 to 7. (Cancelled)

8. (Currently Amended) A structure having pores according to claim 5 1, wherein the material filled in at least one pore disposed above the electroconductive layer is in electrical contact with the electroconductive layer.

9. (Currently Amended) A structure having pores according to ~~any~~ either one of claims ~~5 to 1~~ and 1 and 8, wherein the material filled in at least one pore disposed above the electroconductive layer is an electroconductive material.

10. (Currently Amended) A structure having pores according to claim 5 1, wherein the material filled in at least one pore disposed above the electroconductive layer is a magnetic material.

11. (Withdrawn, Currently Amended) A structure having pores according to claim 5 1, wherein the material filled in at least one pore disposed above the electroconductive layer has a light-emitting function.

12. (Re-presented - Formerly Dependent Claim 16) A structure having pores according to ~~Claim 46~~ comprising:

a substrate;

an electroconductive layer formed on a surface of the substrate, wherein the electroconductive layer is patterned;

a layer containing aluminum oxide covering the electroconductive layer and a surface of the substrate where no electroconductive layer is formed;

a plurality of pores formed in the layer containing aluminum oxide,

wherein the plurality of pores is disposed above the electroconductive layer and the surface of the substrate where no electroconductive layer is formed,

wherein an electroconductive path is provided between the electroconductive layer and the bottom of the pores disposed above the electroconductive layer,

wherein a part of the layer containing aluminum oxide is provided under the plurality of pores, and

wherein the layer containing aluminum oxide provided between the electroconductive layer and the bottom of the pores disposed above the electroconductive layer comprises a material forming the electroconductive layer, and

wherein a material different from aluminum oxide is filled in at least one pore disposed above the electroconductive layer.

13. (Original) A structure having pores according to claim 12, wherein the electroconductive layer comprises at least one element selected from the group consisting of Ti, Zr, Hf, Nb, Ta, Mo, and W.

14. (Original) A structure having pores according to either one of claims 12 and 13, wherein the substrate comprises an insulating material.

15. (Original) A structure having pores according to either one of claims 12 and 13, wherein the substrate comprises an electroconductive substrate and a film composed of an insulating material provided on a surface of the electroconductive substrate.

16 to 18. (Cancelled)

19. (Currently Amended) A structure having pores according to any one of ~~Claims 16 to 18~~ claim 12, wherein the material filled in at least one pore disposed above the electroconductive layer is in electrical contact with the electroconductive layer.

20. (Currently Amended) A structure having pores according to ~~any one of~~
~~Claims 16 to 18~~ claim 12, wherein the material filled in at least one pore disposed above
the electroconductive layer is an electroconductive material.

21. (Currently Amended) A structure having pores according to claim ~~16~~
12, wherein the material filled in at least one pore disposed above the electroconductive
layer is a magnetic material.

22. (Withdrawn, Currently Amended) A structure having pores according
to claim ~~16~~ 12, wherein the material filled in at least one pore disposed above the
electroconductive layer has a light-emitting function.

23. (Withdrawn, Currently Amended) An electron-emitting device
comprising ~~an electron-emitting material provided in at least one pore of~~ a structure having
pores according to claim 12, wherein the material filled in at least one pore disposed above
the electroconductive layer is an electron-emitting material.

24. (Currently Amended) A magnetic device comprising a magnetic
~~material provided in at least one pore of~~ a structure having pores according to claim 12,
wherein the material filled in at least one pore disposed above the electroconductive layer is
a magnetic material.

25. (Withdrawn, Currently Amended) A light-emitting device comprising a ~~light-emitting material provided in at least one pore of a structure having pores according to claim 12, wherein the material filled in at least one pore disposed above the~~ electroconductive layer is a light-emitting material.

26. (Withdrawn, Currently Amended) A method for manufacturing a structure having pores comprising the steps of:

preparing a substrate;

forming a plurality of electroconductive layers each composed of at least one element selected from the group consisting of Ti, Zr, Hf, Nb, Ta, Mo, and W on a part of a surface of the substrate;

forming a film containing aluminum so as to cover the plurality of electroconductive layers and a surface of the substrate having no electroconductive layer thereon; and

anodizing the film containing aluminum so as to form a layer containing aluminum oxide having a plurality of pores; and

filling a material different from aluminum oxide in at least one pore disposed above the electroconductive layer,

wherein the plurality of pores is formed above the electroconductive layer and the surface of the substrate having no electroconductive layer thereon,

wherein a part of the layer containing aluminum oxide is provided under the plurality of pores, and

wherein a material forming the electroconductive layer is diffused to a part of the layer containing aluminum oxide provided between the electroconductive layer and the bottom of the pores above the electroconductive layer.

27. (Withdrawn, Original) A method for manufacturing a structure having pores according to claim 26, wherein the substrate comprises an insulating material.

28. (Withdrawn, Original) A method for manufacturing a structure having pores according to claim 26, wherein the substrate comprises an electroconductive substrate and a film composed of an insulating material provided on the electroconductive substrate.

29. (Withdrawn, Previously Amended) A method for manufacturing a structure having pores according to claim 26, wherein the electroconductive layer is an electroconductive film formed on the surface of the substrate, and the film containing aluminum is formed so that the thickness thereof is not less than two times the thickness of the electroconductive layer.

30. (Withdrawn, Previously Amended) A method for manufacturing a structure having pores according to claim 26, wherein the electroconductive layer is an electroconductive film formed on the surface of the substrate, and the film containing aluminum is formed so that the thickness thereof is not less than five times the thickness of the electroconductive layer.

31. (Withdrawn, Previously Amended) A method for manufacturing a structure having pores according to claim 26, wherein the electroconductive layer is an electroconductive film formed on the surface of the substrate, and the film containing aluminum is formed so that the thickness thereof is not less than ten times the thickness of the electroconductive layer.

32. (Withdrawn, Original) A method for manufacturing a structure having pores according to claim 26, further comprising a step of increasing the diameter of the pores by etching after the anodizing step.

33. (Withdrawn, Previously Amended) A method for manufacturing a structure having pores according to claim 26, further comprising a step, prior to the anodizing step, of forming a recess on a surface of the film containing aluminum disposed so as to cover the plurality of electroconductive layers and the surface of the substrate having no electroconductive layer thereon.

34. (Withdrawn, Currently Amended) A method for manufacturing a structure having pores according to claim 26, wherein the material filled ~~further comprising a step of depositing a material selectively~~ in at least one pore disposed above the electroconductive layer is deposited selectively by applying a voltage thereto in a solution, and wherein the material filled in at least one pore disposed above the electroconductive layer deposited in the pore by electrodeposition is ionized in the solution.

35. (Withdrawn, Original) A method for manufacturing a structure having pores according to claim 34, wherein the voltage applied to the electroconductive layer is an alternating voltage or a pulse voltage.

36. (Withdrawn, Currently Amended) A method for manufacturing a structure having pores comprising the steps of:

preparing a substrate;

forming a patterned electroconductive layer composed of at least one element selected from the group consisting of Ti, Zr, Hf, Nb, Ta, Mo, and W on a part of a surface of the substrate;

forming a film containing aluminum so as to cover the electroconductive layer and a surface of the substrate having no electroconductive layer thereon; ~~and~~

anodizing the film containing aluminum so as to form a layer containing aluminum oxide having a plurality of pores; and

filling a material different from aluminum oxide in at least one pore disposed above the electroconductive layer,

wherein the plurality of pores is formed above the electroconductive layer and the surface of the substrate having no electroconductive layer thereon,

wherein a part of the layer containing aluminum oxide is provided under the plurality of pores, and

wherein a material forming the electroconductive layer is diffused to a part of the layer containing aluminum oxide provided between the electroconductive layer and the bottom of the pores above the electroconductive layer.

37. (Withdrawn, Original) A method for manufacturing a structure having pores according to claim 36, wherein the substrate comprises an insulating material.

38. (Withdrawn, Original) A method for manufacturing a structure having pores according to claim 36, wherein the substrate comprises an electroconductive substrate and a film composed of an insulating material provided on the electroconductive substrate.

39. (Withdrawn, Previously Amended) A method for manufacturing a structure having pores according to claim 36, wherein the electroconductive layer is an electroconductive film formed on the surface of the substrate, and the film containing aluminum is formed so that the thickness thereof is not less than two times the thickness of the electroconductive layer.

40. (Withdrawn, Previously Amended) A method for manufacturing a structure having pores according to claim 36, wherein the electroconductive layer is an electroconductive film formed on the surface of the substrate, and the film containing aluminum is formed so that the thickness thereof is not less than five times the thickness of the electroconductive layer.

41. (Withdrawn, Previously Amended) A method for manufacturing a structure having pores according to claim 36, wherein the electroconductive layer is an electroconductive film formed on the surface of the substrate, and the film containing

aluminum is formed so that the thickness thereof is not less than ten times the thickness of the electroconductive layer.

42. (Withdrawn, Original) A method for manufacturing a structure having pores according to claim 36, further comprising a step of increasing the diameter of the pores by etching after the anodizing step.

43. (Withdrawn, Previously Amended) A method for manufacturing a structure having pores according to claim 36, further comprising a step, prior to the anodizing step, of forming a recess on a surface of the film containing aluminum disposed so as to cover the electroconductive layer and the surface of the substrate having no electroconductive layer thereon.

44. (Withdrawn, Currently Amended) A method for manufacturing a structure having pores according to claim 36, wherein the material filled ~~further comprising a step of depositing a material selectively~~ in at least one pore disposed above the electroconductive layer is deposited selectively by applying a voltage thereto in a solution, and wherein the material filled in at least one pore disposed above the electroconductive layer deposited in the pore by electrodeposition is ionized in the solution.

45. (Withdrawn, Original) A method for manufacturing a structure having pores according to claim 44, wherein the voltage applied to the electroconductive layer is an alternating voltage or a pulse voltage.

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C + P1

46. ~~(Cancelled).~~